



H-811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

N. KOFUJI et al

Serial No. 09/363,191

Group Art Unit: 1763

Filed: July 29, 1999

Examiner: L. Alejandro Mulero

For: DRY ETCHING APPARATUS AND A METHOD OF
MANUFACTURING A SEMICONDUCTOR DEVICE

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

OCT 25 2001

Sir:

In response to the Office Action dated May 22, 2001,
please amend the above-identified application as follows.
A Petition and fee for a two-month Extension of Time also
accompany this response.

IN THE SPECIFICATION

Pages 6 and 7, the paragraph bridging these pages from
page 6, line 19 to page 7, line 7, replace the bridging
paragraph with:

In addition, the stable plasma can be formed even in the
low-pressure and low-density plasma by using high frequency of
the Ultra High Frequency band as high frequency applied in
discoidal electrode 3, in this apparatus. In addition, next
two contrivance did in order to form the plasma of axisymmetry